

*CLAIM AMENDMENTS*

1. (Currently Amended) A solid-state imaging device comprising ~~the following in the same;~~

a semiconductor substrate;

a photodiode in the semiconductor substrate;

a circuit element that is adjacent to the photodiode in the semiconductor substrate;

~~and~~

a device isolation that is on the semiconductor substrate and adjacent to the photodiode in the same semiconductor substrate, wherein;

a light-incident surface protecting film on a light-incident surface of the photodiode and including an opening exposing a central portion of the light-incident surface of the photodiode; and

an antireflection film that is out of contact with not overlapping the device isolation is provided over the light-receiving, covering the central region of the light-incident surface of the photodiode that is exposed by the opening, and extending onto the light-incident surface protecting film adjacent the opening to a first side surface facing the device isolation and a second side surface facing the circuit element.

2. (Currently Amended) The solid-state imaging device according to Claim 1, wherein ~~an end~~ the first side surface of the antireflection film ~~on~~ at the device isolation side is spaced ~~by~~ a predetermined distance ~~away~~ from the device isolation.

Claims 3-5 (Cancelled).

6. (Currently Amended) A solid-state imaging device comprising ~~the following in the same;~~

a semiconductor substrate;

a photodiode in the semiconductor substrate;

a circuit element that is adjacent to the photodiode in the semiconductor substrate;

~~and~~

a device isolation that is on the semiconductor substrate and adjacent to the photodiode, wherein;

a light-incident surface protecting film on a light-incident surface of the photodiode and including an opening exposing a central portion of the light-incident surface of the photodiode; and

an antireflection film ~~that is out of contact with~~ not overlapping the device isolation ~~and, not overlapping the circuit element is provided over,~~ covering the central region of the ~~light-receiving~~ light-incident surface of the photodiode ~~that is exposed by the opening,~~ and extending onto the light-incident surface protecting film adjacent the opening to a first side surface facing the device isolation and a second side surface facing the circuit element.

7. (Currently Amended) The solid-state imaging device according to Claim 6, wherein ~~one end~~ the first side surface of the antireflection film ~~on~~ facing the device isolation ~~side~~ is spaced ~~by a first predetermined distance away~~ from the device isolation, and ~~the other end~~ the second side surface of the antireflection film ~~on~~ facing the circuit element ~~side~~ is spaced ~~by a second predetermined distance away~~ from the circuit element.

Claim 8 (Cancelled).

9. (Currently Amended) The solid-state imaging device according to Claim 6, ~~comprising a plurality of insulating films that cover wherein the light-receiving light-incident surface of the photodiode, located over the light-receiving surface of the photodiode, wherein the protecting film comprises a plurality of insulating films have a penetrating hole that exposes the light-receiving surface of the photodiode, and the antireflection film covers the light-receiving surface of the photodiode, which is exposed from the penetrating hole.~~

Claims 10 and 11 (Cancelled).

12. (Currently Amended) ~~A~~ The solid-state imaging device comprising the following in the same semiconductor substrate, a photodiode, a circuit element that is adjacent to the photodiode, and a device isolation that is adjacent to the photodiode, wherein an according to claim 1, wherein the antireflection film ~~formed of~~ is a silicon oxynitride film ~~is provided over the light-receiving surface of the photodiode.~~